

# SOT223 NPN SILICON PLANAR HIGH PERFORMANCE TRANSISTOR

FZT655

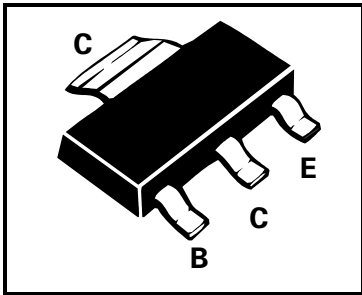
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## FEATURES

\* Low saturation voltage

COMPLEMENTARY TYPE – FZT755

PARTMARKING DETAIL – FZT655



## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	150	V
Collector-Emitter Voltage	$V_{CEO}$	150	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Peak Pulse Current	$I_{CM}$	2	A
Continuous Collector Current	$I_C$	1	A
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	150			V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	150			V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu A$
Collector Cut-Off Current	$I_{CBO}$			0.1	$\mu A$	$V_{CB}=125V$
Emitter Cut-Off Current	$I_{EBO}$			0.1	$\mu A$	$V_{EB}=3V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.5 0.5	V	$I_C=500mA, I_B=50mA^*$ $I_C=1A, I_B=200mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.1	V	$I_C=500mA, I_B=50mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1.0	V	$I_C=500mA, V_{CE}=5V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	50 50 20		300		$I_C=10mA, V_{CE}=5V^*$ $I_C=500mA, V_{CE}=5V^*$ $I_C=1A, V_{CE}=5V^*$
Transition Frequency	$f_T$	30			MHz	$I_C=10mA, V_{CE}=20V$ $f=20MHz$
Output Capacitance	$C_{obo}$			20	pF	$V_{CB}=10V, f=1MHz$

\*Measured under pulsed conditions. Pulse Width=300 $\mu s$ . Duty cycle  $\leq 2\%$

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## TYPICAL CHARACTERISTICS

